TRANSISTOR (NPN) **Plastic-Encapsulate Transistor**

FEATURES

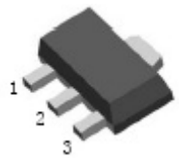
- Power dissipation

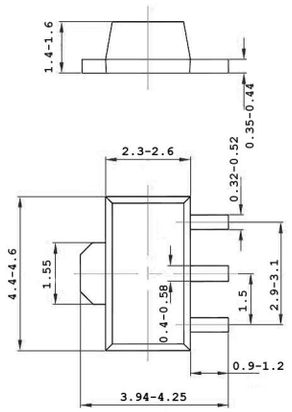
  P_D : 0.5W(Ta=25℃)

MARKING: DBP, DBQ, DBR

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER





UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	2	mA
Collector Dissipation	P_C	500	mW
Junction and Storage Temperature	T_J, T_{stg}	-55-150	℃

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=50μA, I_E=0	40			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	32			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=50μA, I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V, I_E=0			1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4V, I_C=0			1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=3V, I_C=500mA	82		390	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2A, I_B=0.2A			0.8	V
Transition Frequency	f_T	V_{CE}=5V, I_C=50mA, f=100MHz		100		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		30		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390

RoHS Pb-free TIP Semiconductor